

# Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V <sub>DSS</sub>	-20	V
Gate-Source Voltage (Note 7)			V <sub>GSS</sub>	±10	V
Continuous Drain Current (Note 9) $V_{GS}$ = -10V	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	I <sub>D</sub>	-4.3 -3.4	A
	t<5s	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	۱ <sub>D</sub>	-5.5 -4.3	A
Maximum Continuous Body Diodes Forward Current (Note 9)			ls	-2	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I <sub>DM</sub>	-30	А
Pulsed Body Diodes Forward Current (10µs Pulse, Duty Cycle = 1%)			I <sub>SM</sub>	-30	А

## **Thermal Characteristics**

Characteristic		Symbol	Value	Unit
Total Dower Dissinction (Note 9)	T <sub>A</sub> = +25°C	Р	0.8	W
Total Power Dissipation (Note 8)	$T_A = +70^{\circ}C$	PD	0.5	
Thermal Resistance, Junction to Ambient (Note 8)	Steady State	D	161	°C/W
	t<5s	R <sub>0JA</sub>	96	
Total Power Dissipation (Note 9)	T <sub>A</sub> = +25°C	P	1.3	W
	T <sub>A</sub> = +70°C	PD	0.8	
Thermal Desistance, Junction to Ambient (Note 0)	Steady State	D	99	°C/W
Thermal Resistance, Junction to Ambient (Note 9)	t<5s	$R_{\theta JA}$	60	
Thermal Resistance, Junction to Case (Note 9)		R <sub>θJC</sub>	15	
Operating and Storage Temperature Range		TJ, T <sub>STG</sub>	-55 to +150	°C

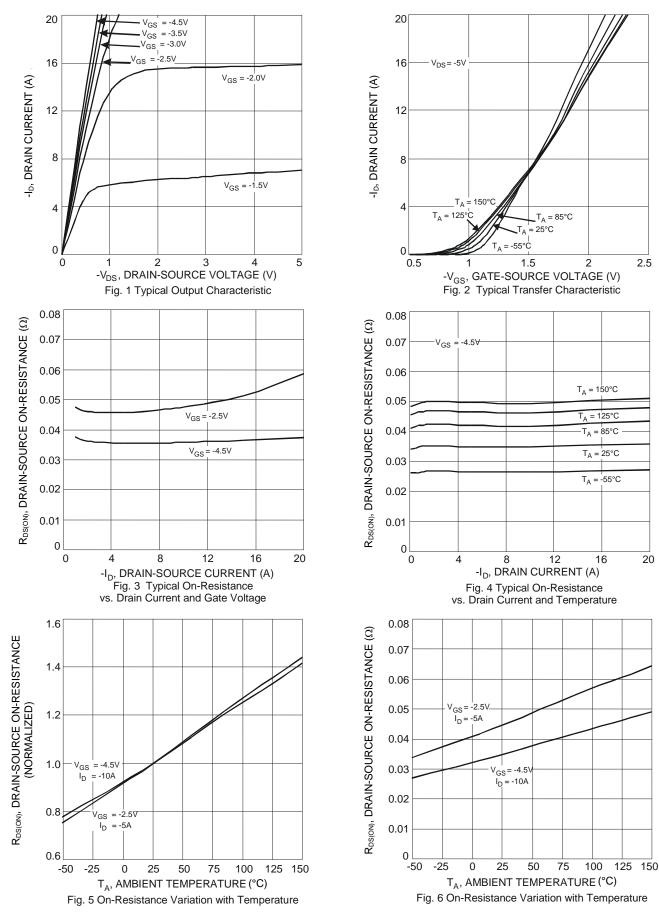
### Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 10)	Cymbol		1.76	max	Onic	Test condition
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-20	_	_	V	$V_{GS} = 0V, I_{D} = -250\mu A$
Zero Gate Voltage Drain Current	IDSS	_	_	-1	μA	$V_{DS} = -20V, V_{GS} = 0V$
Gate-Source Leakage	IGSS		—	±10	μA	$V_{GS} = \pm 8V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 10)						÷
Gate Threshold Voltage	V <sub>GS(TH)</sub>	-0.3	_	-1.4	V	$V_{DS} = V_{GS}, I_D = -250 \mu A$
			25	38		$V_{GS} = -10V, I_D = -3.5A$
Static Drain-Source On-Resistance	D		29	43	mΩ	$V_{GS} = -4.5V, I_D = -3A$
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	37	75	mΩ	V <sub>GS</sub> = -2.5V, I <sub>D</sub> = -1A
		_	47	_		V <sub>GS</sub> = -1.8V, I <sub>D</sub> = -0.5A
Forward Transfer Admittance	Y <sub>fs</sub>	—	3	—	S	$V_{DS} = -5V, I_D = -4A$
DYNAMIC CHARACTERISTICS (Note 11)						·
Input Capacitance	Ciss		216	—	pF	\/ 45\/ \/ Q\/
Output Capacitance	Coss		90	-	pF	−V <sub>DS</sub> = -15V, V <sub>GS</sub> = 0V −f = 1.0MHz
Reverse Transfer Capacitance	C <sub>rss</sub>		24	—	pF	
Gate Resistnace	Rg	_	250	—	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$
SWITCHING CHARACTERISTICS (Note 11)						·
Total Gate Charge	Qg		9.1	-	nC	
Gate-Source Charge	Q <sub>gs</sub>	_	1.6	_	nC	$V_{GS} = -4.5V, V_{DS} = -10V$
Gate-Drain Charge	Q <sub>qd</sub>	_	2.0	—	nC	$-I_D = -4A$
Turn-On Delay Time	t <sub>D(ON)</sub>	—	80	—	ns	
Turn-On Rise Time	t <sub>R</sub>	-	155	—	ns	V <sub>DS</sub> = -10V, V <sub>GS</sub> = -4.5V,
Turn-Off Delay Time	t <sub>D(OFF)</sub>		688	—	ns	$R_D = 2.5\Omega, R_G = 3.0\Omega$
Turn-Off Fall Time	t <sub>F</sub>		423	—	ns	7

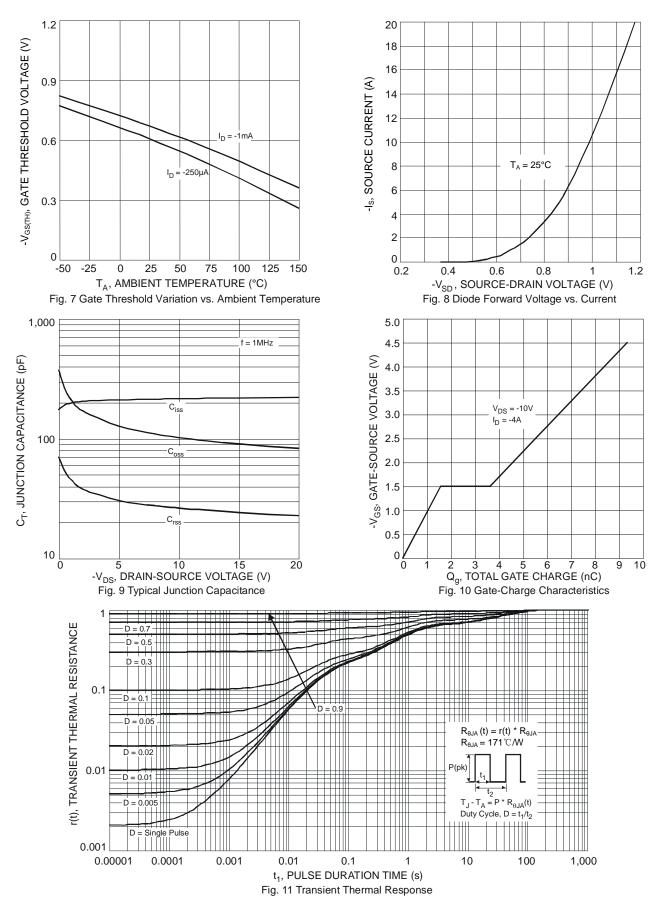
7. AEC-Q101  $V_{GS}$  maximum is  $\pm 9.6V.$ Notes:

AEC-Q101 V<sub>GS</sub> maximum is ±9.6V.
Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
Short duration pulse test used to minimize self-heating effect.
Guaranteed by design. Not subject to product testing.







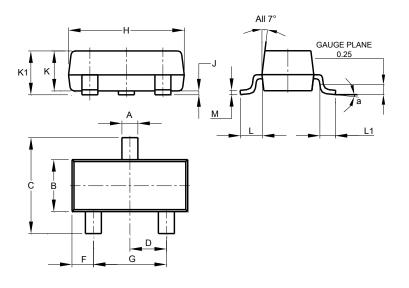




### **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

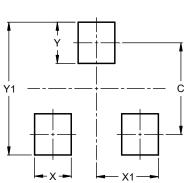
SOT23



	SOT23					
Dim	Min	Max	Тур			
Α	0.37	0.51	0.40			
В	1.20	1.40	1.30			
С	2.30	2.50	2.40			
D	0.89	1.03	0.915			
F	0.45	0.60	0.535			
G	1.78	2.05	1.83			
н	2.80	3.00	2.90			
J	0.013	0.10	0.05			
К	0.890	1.00	0.975			
K1	0.903	1.10	1.025			
L	0.45	0.61	0.55			
L1	0.25	0.55	0.40			
М	0.085	0.150	0.110			
а	0°	8°				
All	All Dimensions in mm					

## **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.



SOT23

Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Y	0.9
Y1	2.9



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